

Electronic Supplementary Information (ESI)

Dielectric Elastomer Actuator with Excellent Electromechanical Performance by Slide-Ring Materials/Barium Titanate Composites[†]

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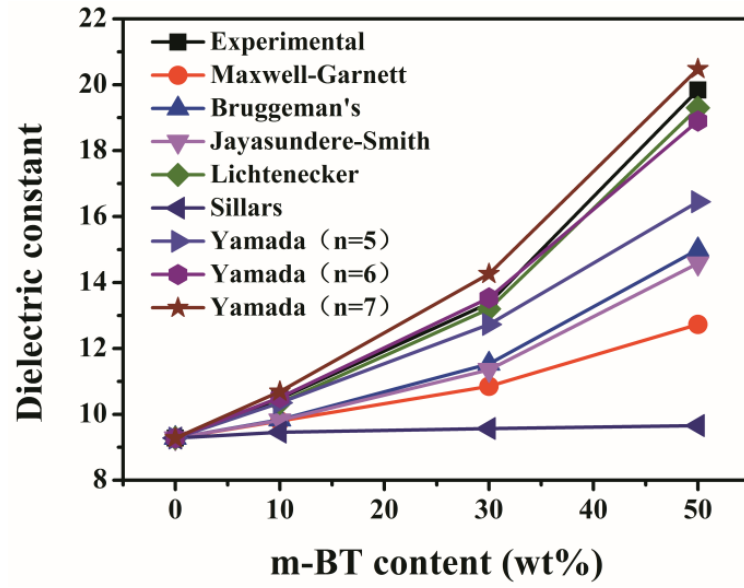


Figure S-1 Comparison of measured dielectric constant (at 1 kHz) of m-BT/SR4 composites with values predicted by various dielectric mixing rules.

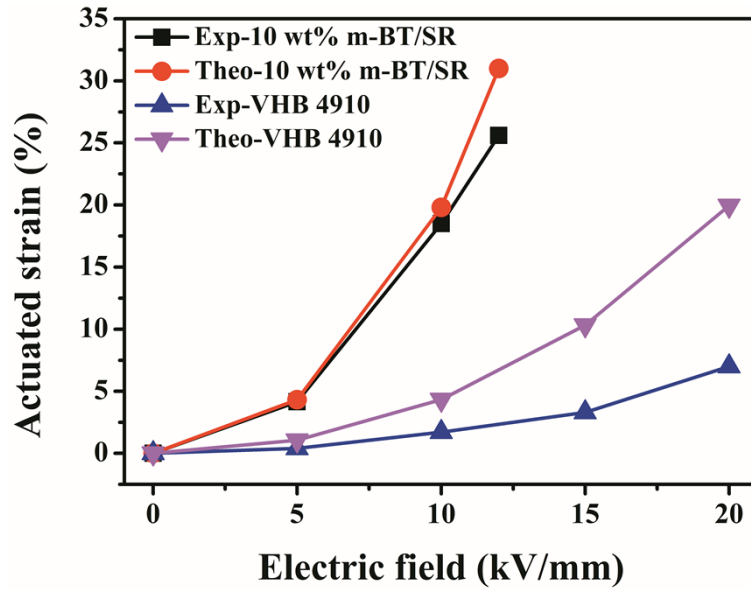


Figure S-2 Comparison of theoretical and experimental actuated strains of 10 wt% m-BT/SR4 composite and VHB 4910 (the dielectric constant of VHB 4910 used in this calculation is 4.7 and the elastic modulus of VHB 4910 used in this calculation is

0.1MPa according to our measurement).

Table S-1 Comparing actuated strain of slide-ring materials actuator with other EAP actuators

Material	Pre-strains (x, y) (%)	Actuated strain ^{a)} (%)	Field strength ^{a)} (kV mm ⁻¹)	Ref
VHB 4910	540, 75	215	239	[1]
VHB 4905	300, 300	200	480	[2]
Silicone ENP SEBS 161(5-30 wt%)	300, 300	180-30	32-133	[3]
Silicone ENP SEBS 217(5-30 wt%)	300, 300	245-47	22-98	[3]
VHB 4910	300, 300	158	412	[1]
VHB4910/poly(1,6-hexanediol diacrylate)	275, 275	233	300	[4]
HS3	280, 0	117	128	[1]
Silicone-based prototype	200 ^{b)}	18.31	96	[5]
TiO ₂ /SEBS	100, 100	12	27.5	[6]
PMMA-PnBA-PMMA	100, 100	12	4.5	[7]
30 wt% TiO ₂ /silicone	100, 100	11	10	[8]
PDMS/PHT	100, 100	7.6	8	[9]
Polyurethane-based prototype	100 ^{b)}	2.04	127	[5]
CF19-218	100, 0	63	181	[1]
HS3 silicone	68, 68	93	110	[1]
CF19-2186 silicone	45, 45	64	350	[1]
DC 3481(5% 81-R)/20 wt% CPO	40, 40	11	27	[10]
Silicone elastomer C1	30, 30	40	12.4	[11]

CF19-2186 silicone	15, 15	33	160	[1]
VHB 4910 acrylic	15, 15	40	55	[1]
HS3 silicone	14, 14	69	72	[1]
Allyl-cyano/SiR	10, 10	7	20	[12]
TiO ₂ /PDMS	5, 5	18	50	[13]
Dipole/PDMS	5, 5	14.8	1.3	[14]
DOP/HNBR	0, 0	22	30	[15]
MA20	0, 0	2.1 ^{a)}	5	[16]
SEBS20	0, 0	1.4 ^{a)}	5	[16]
MBM104 ATPEG	0, 0	50	65	[17]
TiO ₂ /PDMS/DMSO	0, 0	13	30	[18]
PANI@PDVB/PDMS	0, 0	12	54	[19]
PEG/PDMS	0, 0	11.5	40	[20]
BaTiO ₃ /CB/PDMS	0, 0	7.46	30	[21]
PANI-g-PolyCuPc-g-PU	0, 0	7	23	[22]
23 wt% PANI/P(VDF-TrFE-CTFE)	0, 0	1.5 ^{c)}	9.5	[23]
14PANI/15PolyCuPc/85PU	0, 0	9.3 ^{c)}	20	[24]
SEBS-MA grafted PANI	0, 0	1.4	27	[25]
NBR/TiO ₂ /DOP	0, 0	3.04	20	[26]
18.26% vol% graphite/polyurethane	0, 0	0.037	0.75	[27]
5 wt% CNTs/PDMS	0, 0	4.4	1.5	[28]
P(VDF-TrFE)/40 wt% CuPc	0, 0	1.91	13	[29]
Silicone oil/PMN/PDMS	0, 0	7.4	40	[30]
CNT/P(VDF-TrFE-CFE)	0, 0	2.5	72	[31]

P(VDF-TrFE-CFE)	0, 0	4.5	130	[32]
LC gels	0, 0	2.1	25	[33]
Polyester elastomer	0, 0	11.9	15.6	[34]
6 vol% TiO ₂ /polyester elastomer	0, 0	11.8	9.8	[35]
SR4	0, 0	12	10	
10 wt% m-BT/SR4	0, 0	26	12	

a) Estimated from graphical data in cited reference, when no tabulated results were provided. b) The axial pre-strain. c) The longitudinal strain.

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